

Device Modeling Report

COMPONENTS: BIPOLAR JUNCTION TRANSISTOR
PART NUMBER: 2SD2623
MANUFACTURER: PANASONIC

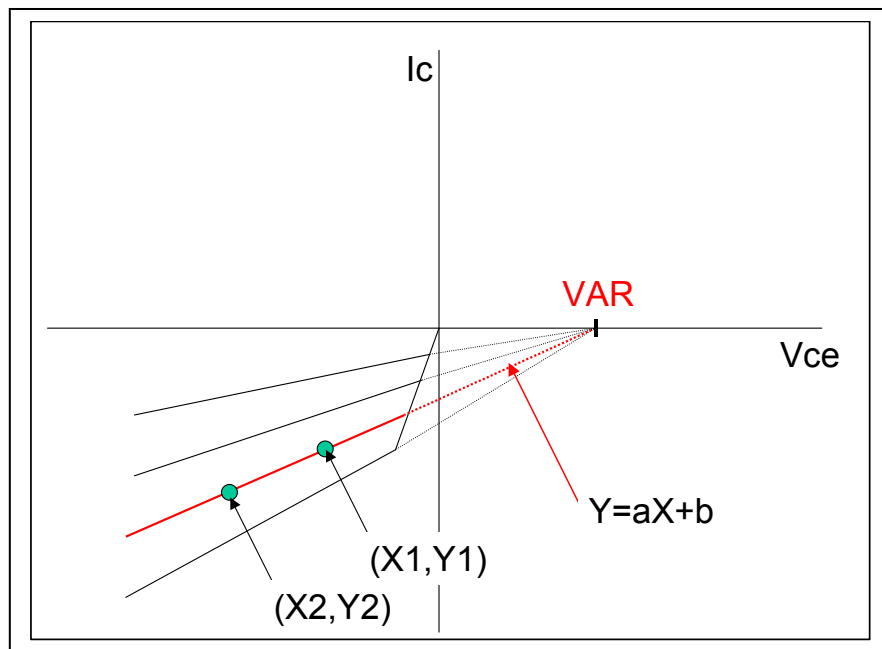
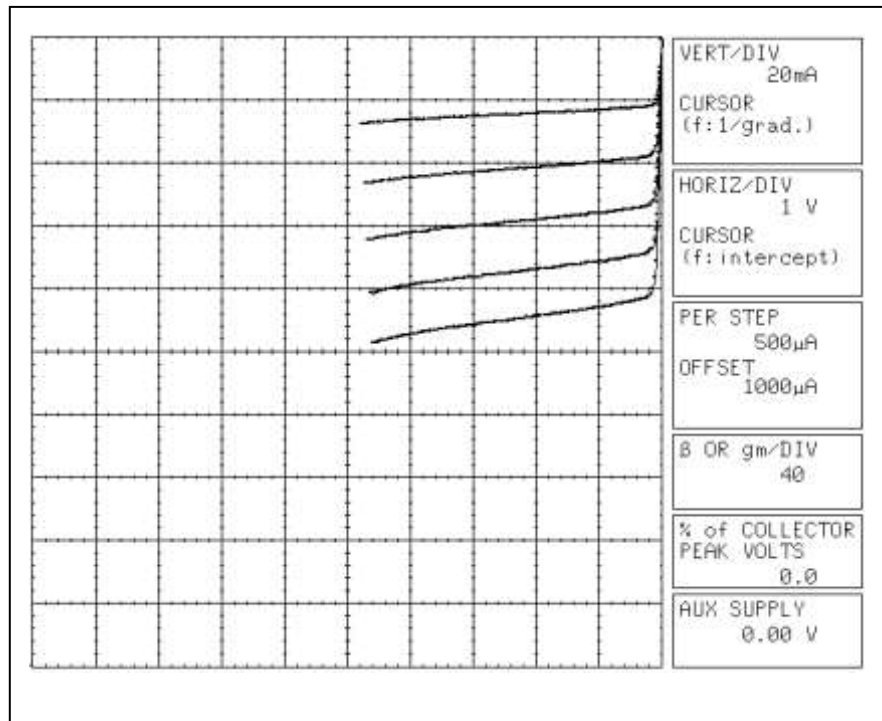


Bee Technologies Inc.

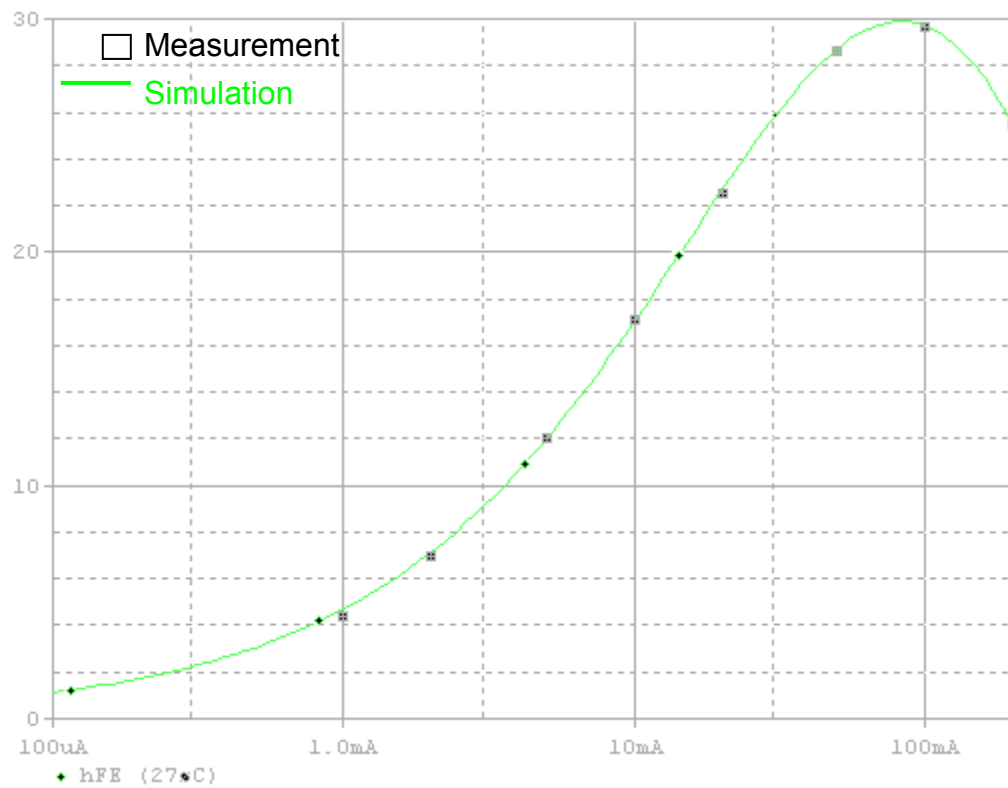
PSpice model parameter	Model description
IS	Saturation Current
BF	Ideal Maximum Forward Beta
NF	Forward Current Emission Coefficient
VAF	Forward Early Voltage
IKF	Forward Beta Roll-off Knee Current
ISE	Non-ideal Base-Emitter Diode Saturation Current
NE	Non-ideal Base-Emitter Diode Emission Coefficient
BR	Ideal Maximum Reverse Beta
NR	Reverse Emission Coefficient
VAR	Reverse Early Voltage
IKR	Reverse Beta Roll-off Knee Current
ISC	Non-ideal Base-Collector Diode Saturation Current
NC	Non-ideal Base-Collector Diode Emission Coefficient
NK	Forward Beta Roll-off Slope Exponent
RE	Emitter Resistance
RB	Base Resistance
RC	Series Collector Resistance
CJE	Zero-bias Emitter-Base Junction Capacitance
VJE	Emitter-Base Junction Potential
MJE	Emitter-Base Junction Grading Coefficient
CJC	Zero-bias Collector-Base Junction Capacitance
VJC	Collector-base Junction Potential
MJC	Collector-base Junction Grading Coefficient
FC	Coefficient for Onset of Forward-bias Depletion Capacitance
TF	Forward Transit Time
XTF	Coefficient for TF Dependency on Vce
VTF	Voltage for TF Dependency on Vce
ITF	Current for TF Dependency on Ic
PTF	Excess Phase at $f=1/2\pi \cdot TF$
TR	Reverse Transit Time
EG	Activation Energy
XTB	Forward Beta Temperature Coefficient
XTI	Temperature Coefficient for IS

Reverse

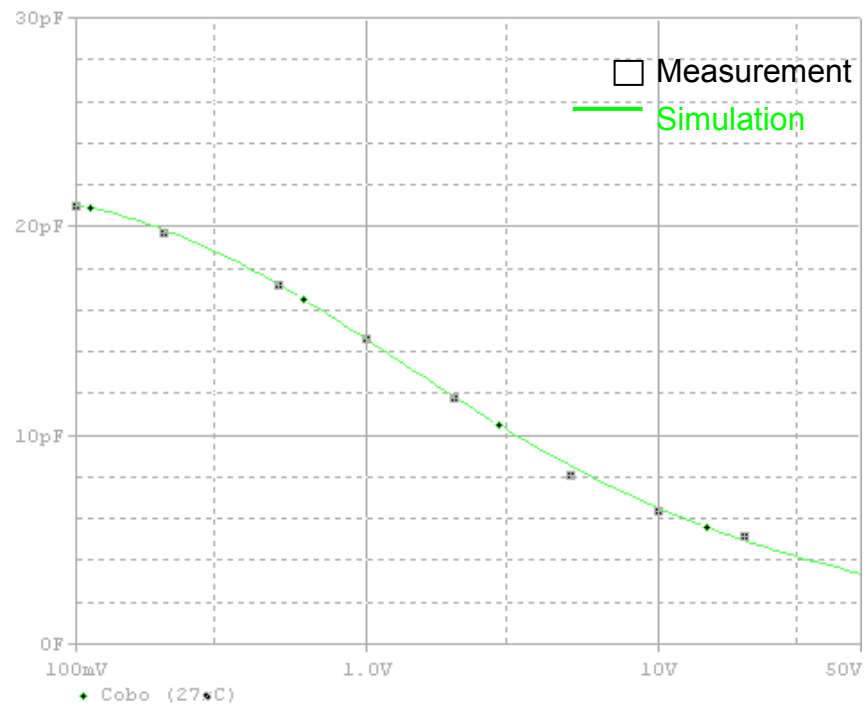
Reverse Early Voltage Characteristic



Reverse DC Beta Characteristic (I_e vs. h_{FE})



C-B Capacitance Characteristic

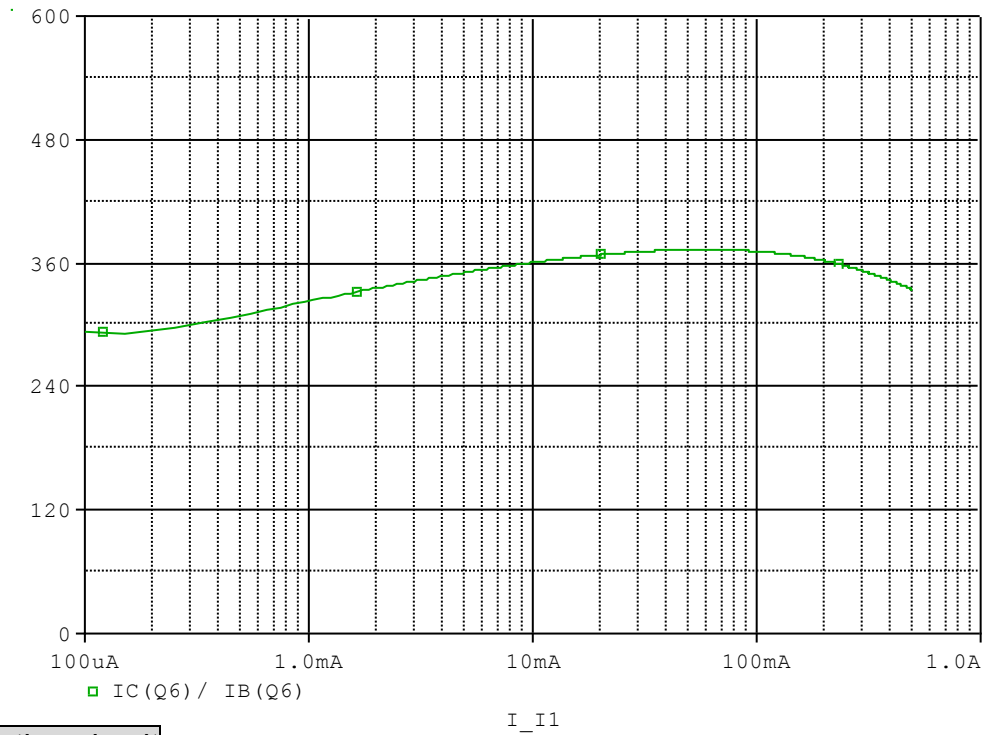


E-B Capacitance Characteristic

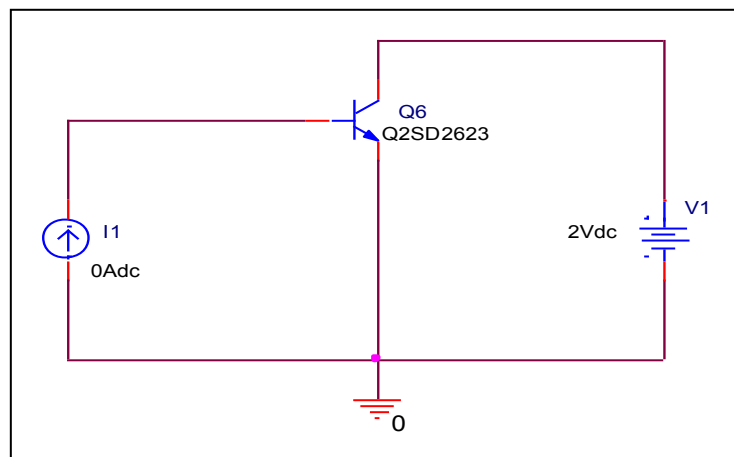


BJT Ic-hFE Characteristics

Circuit simulation result

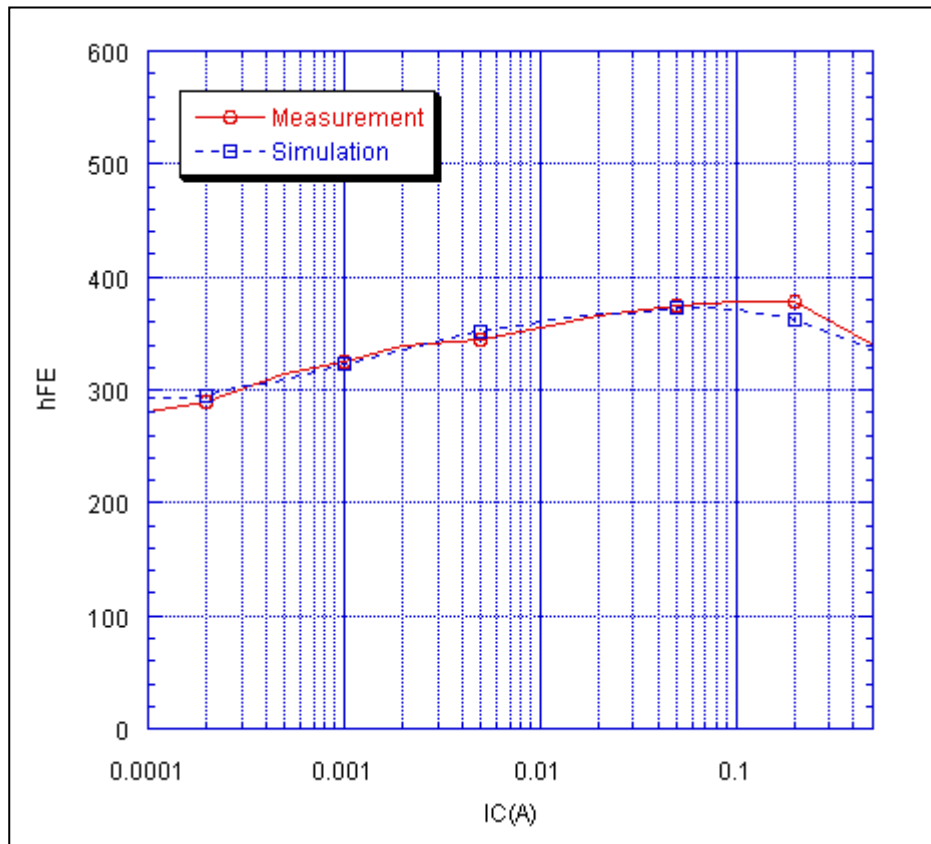


Evaluation circuit



Comparison Graph

Circuit simulation result

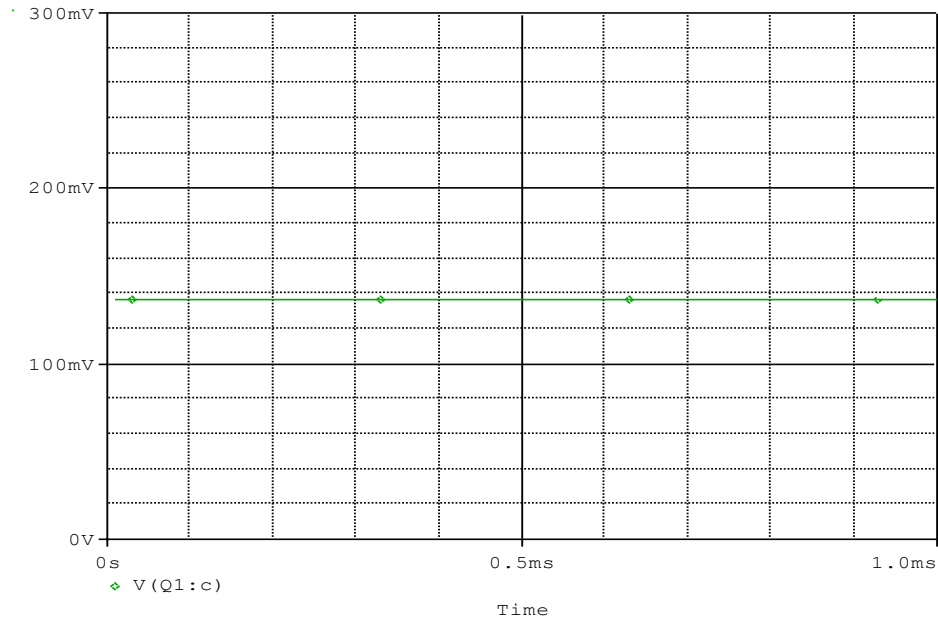


Simulation result

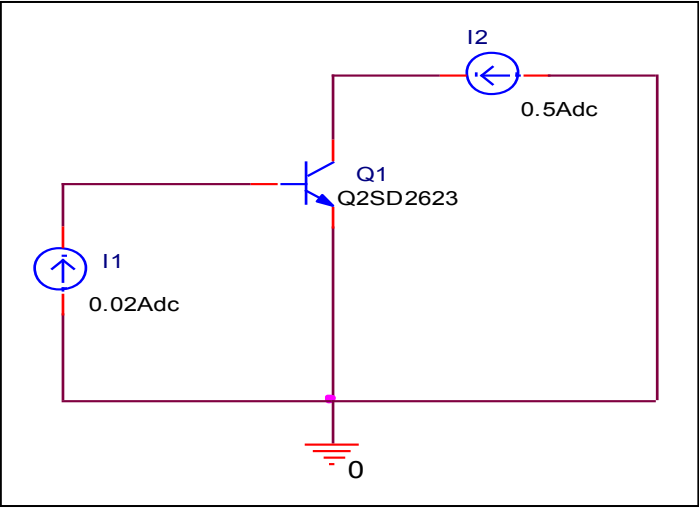
Ic(A)	hFE		%Error
	Measurement	Simulation	
0.0001	280.000	292.946	4.624
0.0002	290.000	294.612	1.590
0.0005	315.000	309.379	-1.784
0.001	325.000	322.610	-0.735
0.002	340.000	335.564	-1.305
0.005	345.000	350.916	1.715
0.010	355.000	360.514	1.553
0.020	365.000	367.889	0.792
0.050	375.000	372.998	-0.534
0.100	378.000	371.373	-1.753
0.200	379.000	362.337	-4.397
0.500	340.000	333.647	-1.869

BJT Vce (sat) voltage Characteristics

Circuit simulation result



Evaluation circuit



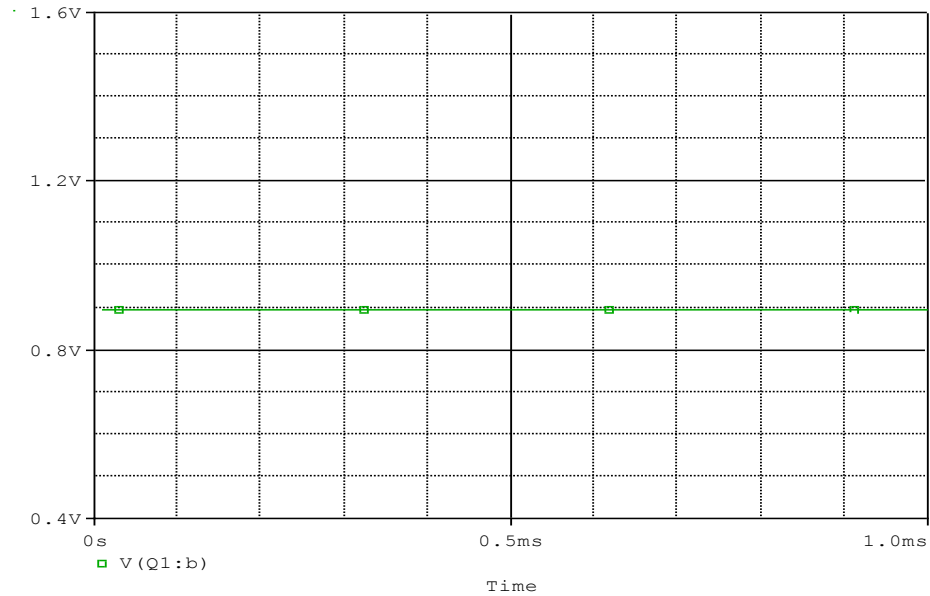
Simulation result

Test condition: $I_C/I_B = 25$, $I_C=0.5A$

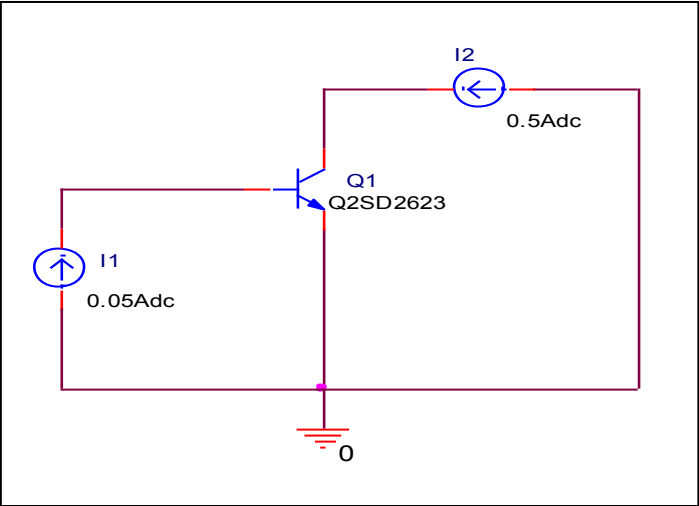
Vce(sat)(V)	Measurement	Simulation	Error(%)
	0.140	0.136	-2.857

BJT Vbe (sat) voltage Characteristics

Circuit simulation result



Evaluation circuit



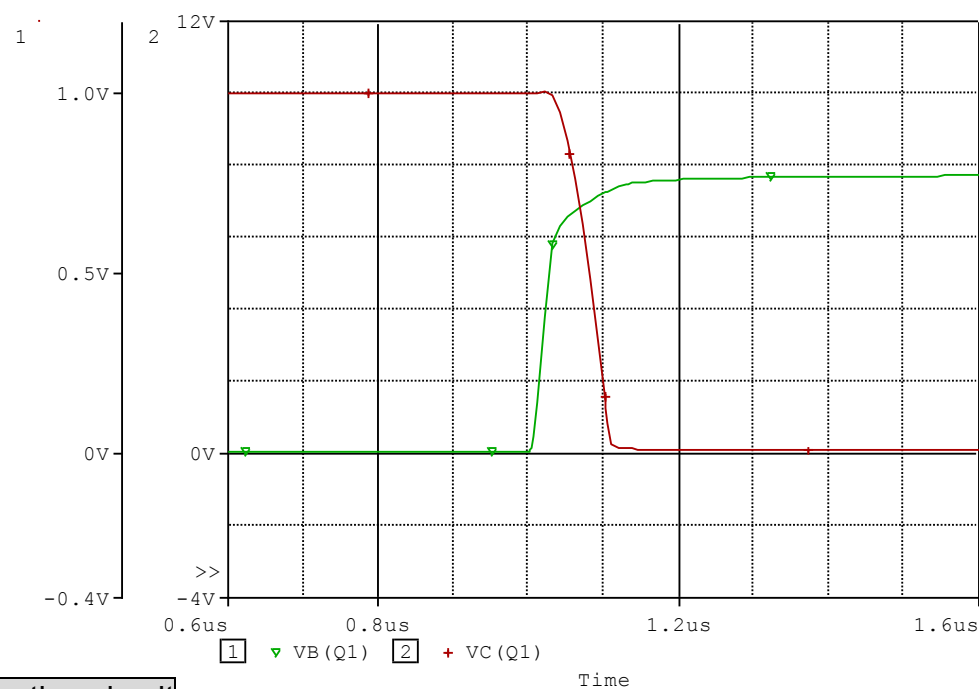
Simulation result

Test condition: $I_C/I_B = 20$, $I_C=0.5A$

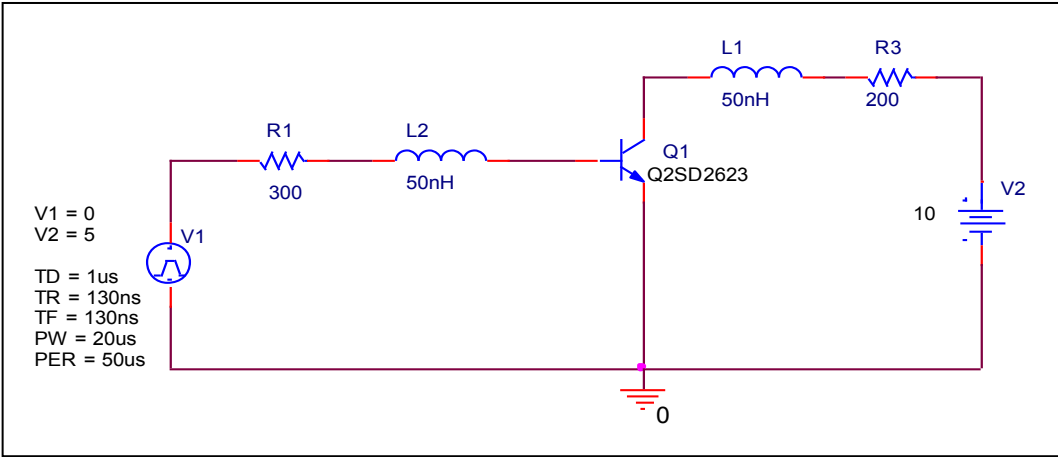
Vbe(sat)(V)	Measurement	Simulation	Error(%)
	1.200(Max)	0.893	-

Switching Characteristics

Circuit simulation result



Evaluation circuit

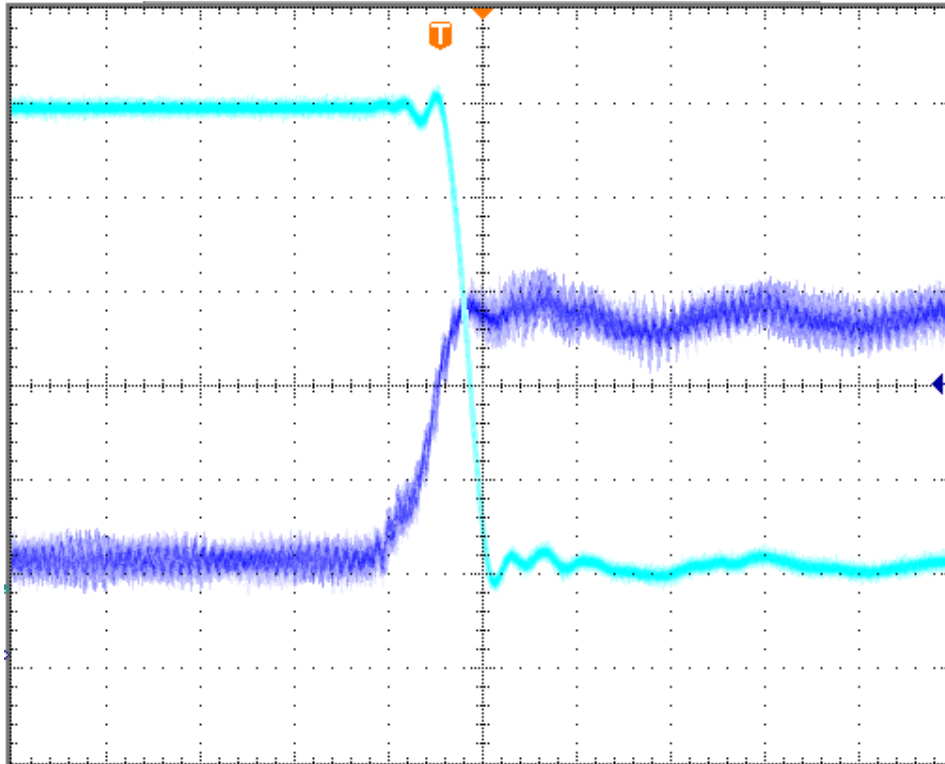


Simulation result

	Measurement	Simulation	%Error
t_{stg} (us)	0.103	0.098	-4.854
t_f (us)	0.054	0.056	3.704

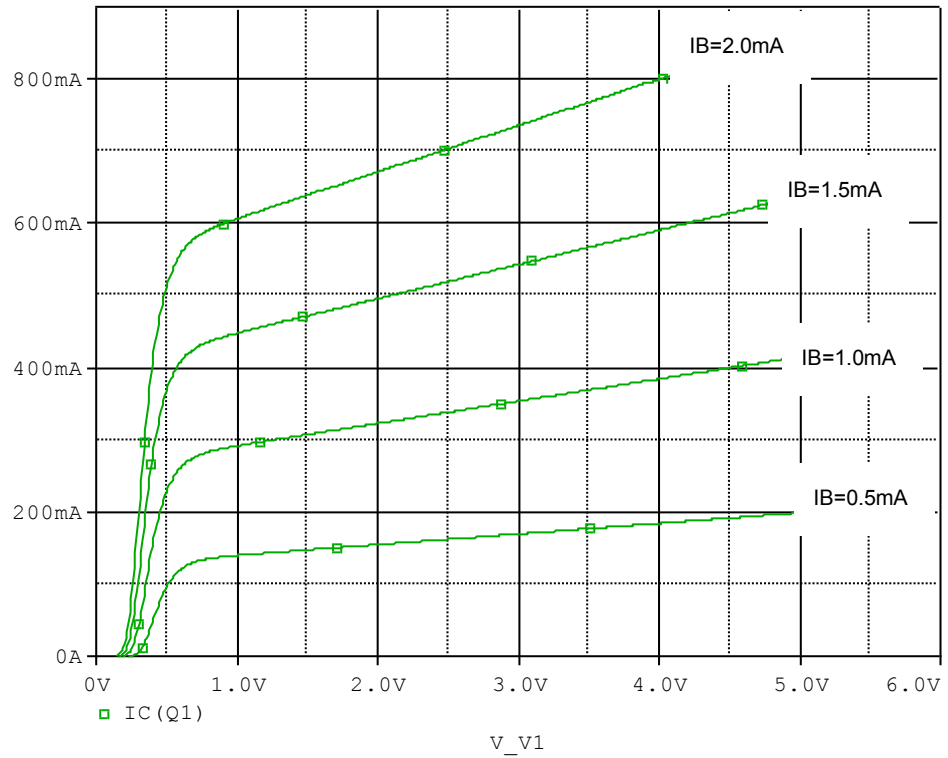
Switching Characteristic

Reference



Output Characteristics

Circuit simulation result



Evaluation circuit

